

## N-Channel Enhancement Mode Power MOSFET

### Description

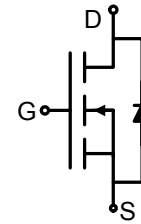
The BLM2304 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a load switch or in PWM applications.

### General Features

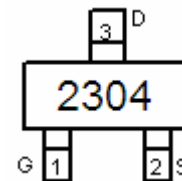
- $V_{DS} = 30V, I_D = 3.6A$   
 $R_{DS(ON)} < 73m\Omega @ V_{GS}=4.5V$   
 $R_{DS(ON)} < 58m\Omega @ V_{GS}=10V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

### Application

- Battery protection
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23 top view

### Package Marking and Ordering Information

| Device Marking | Device  | Device Package | Reel Size | Tape width | Quantity   |
|----------------|---------|----------------|-----------|------------|------------|
| 2304           | BLM2304 | SOT-23         | Ø180mm    | 8 mm       | 3000 units |

### Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

| Parameter  | Symbol         | Limit      | Unit             |
|--|----------------|------------|------------------|
| Drain-Source Voltage                             | $V_{DS}$       | 30         | V                |
| Gate-Source Voltage                              | $V_{GS}$       | $\pm 20$   | V                |
| Drain Current-Continuous                         | $I_D$          | 3.6        | A                |
| Drain Current-Pulsed (Note 1)                    | $I_{DM}$       | 15         | A                |
| Maximum Power Dissipation                        | $P_D$          | 1.7        | W                |
| Operating Junction and Storage Temperature Range | $T_J, T_{STG}$ | -55 To 150 | $^\circ\text{C}$ |

### Thermal Characteristic

|  |                 |      |                    |
|--|-----------------|------|--------------------|
| Thermal Resistance, Junction-to-Ambient (Note 2) | $R_{\theta JA}$ | 73.5 | $^\circ\text{C/W}$ |
|--|-----------------|------|--------------------|

### Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

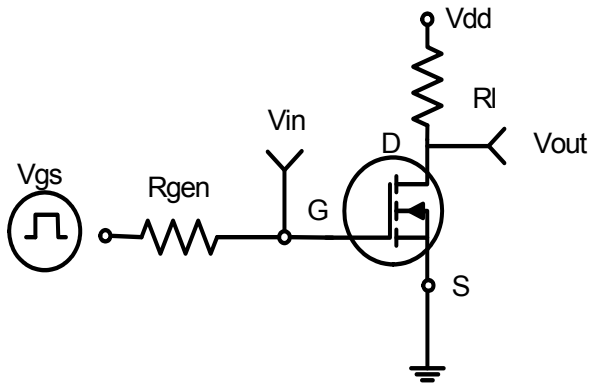
| Parameter                       | Symbol     | Condition                       | Min | Typ | Max | Unit          |
|---------------------------------|------------|---------------------------------|-----|-----|-----|---------------|
| <b>Off Characteristics</b>      |            |                                 |     |     |     |               |
| Drain-Source Breakdown Voltage  | $BV_{DSS}$ | $V_{GS}=0V, I_D=250\mu\text{A}$ | 30  | 33  | -   | V             |
| Zero Gate Voltage Drain Current | $I_{DSS}$  | $V_{DS}=30V, V_{GS}=0V$         | -   | -   | 1   | $\mu\text{A}$ |

|   |              |  |     |      |           |            |
|---|--------------|--|-----|------|-----------|------------|
| Gate-Body Leakage Current                 | $I_{GSS}$    | $V_{GS}=\pm 20V, V_{DS}=0V$                              | -   | -    | $\pm 100$ | nA         |
| <b>On Characteristics (Note 3)</b>        |              |  |     |      |           |            |
| Gate Threshold Voltage                    | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$                            | 1.2 | 1.5  | 2.2       | V          |
| Drain-Source On-State Resistance          | $R_{DS(ON)}$ | $V_{GS}=4.5V, I_D=3.1A$                                  | -   | 58   | 73        | m $\Omega$ |
|   |              | $V_{GS}=10V, I_D=3.6A$                                   | -   | 40   | 58        | m $\Omega$ |
| Forward Transconductance                  | $g_{FS}$     | $V_{DS}=5V, I_D=3.6A$                                    | -   | 11   | -         | S          |
| <b>Dynamic Characteristics (Note4)</b>    |              |  |     |      |           |            |
| Input Capacitance                         | $C_{iss}$    | $V_{DS}=15V, V_{GS}=0V,$<br>$F=1.0MHz$                   | -   | 230  | -         | PF         |
| Output Capacitance                        | $C_{oss}$    |  | -   | 40   | -         | PF         |
| Reverse Transfer Capacitance              | $C_{rss}$    |  | -   | 17   | -         | PF         |
| <b>Switching Characteristics (Note 4)</b> |              |  |     |      |           |            |
| Turn-on Delay Time                        | $t_{d(on)}$  | $V_{DD}=10V, I_D=3.6A$<br>$V_{GS}=4.5V, R_{GEN}=6\Omega$ | -   | 10   | -         | nS         |
| Turn-on Rise Time                         | $t_r$        |  | -   | 50   | -         | nS         |
| Turn-Off Delay Time                       | $t_{d(off)}$ |  | -   | 10   | -         | nS         |
| Turn-Off Fall Time                        | $t_f$        |  | -   | 20   | -         | nS         |
| Total Gate Charge                         | $Q_g$        | $V_{DS}=15V, I_D=3.6A,$<br>$V_{GS}=10V$                  | -   | 4.0  | -         | nC         |
| Gate-Source Charge                        | $Q_{gs}$     |  | -   | 0.75 | -         | nC         |
| Gate-Drain Charge                         | $Q_{gd}$     |  | -   | 0.65 | -         | nC         |
| <b>Drain-Source Diode Characteristics</b> |              |  |     |      |           |            |
| Diode Forward Voltage (Note 3)            | $V_{SD}$     | $V_{GS}=0V, I_S=2.7A$                                    | -   | 0.8  | 1.2       | V          |
| Diode Forward Current (Note 2)            | $I_S$        |  | -   | -    | 1.6       | A          |

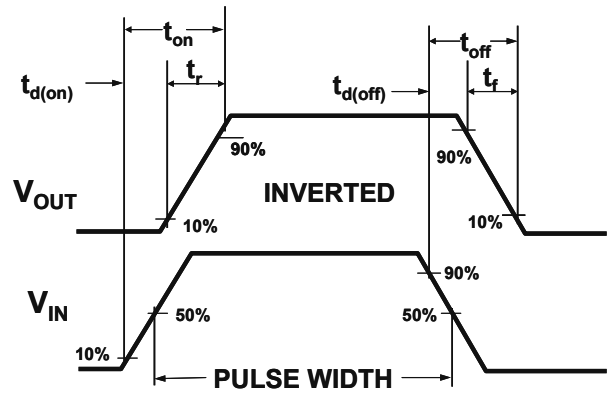
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

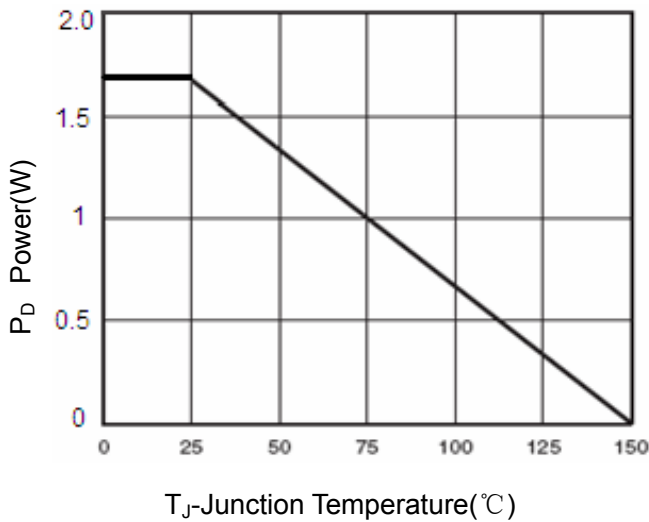
## Typical Electrical and Thermal Characteristics



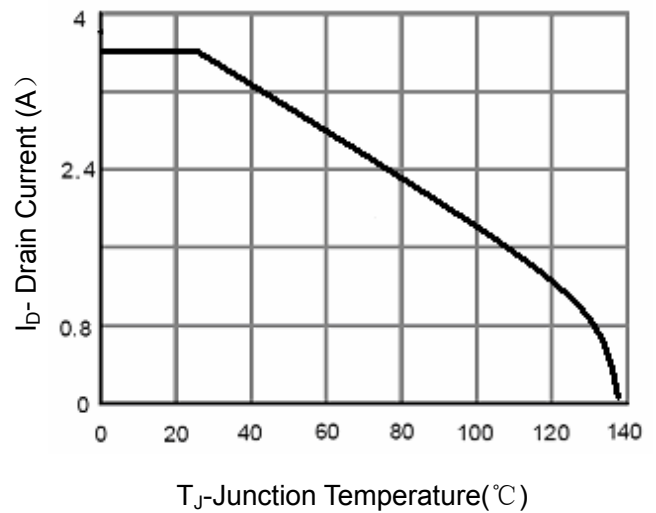
**Figure 1: Switching Test Circuit**



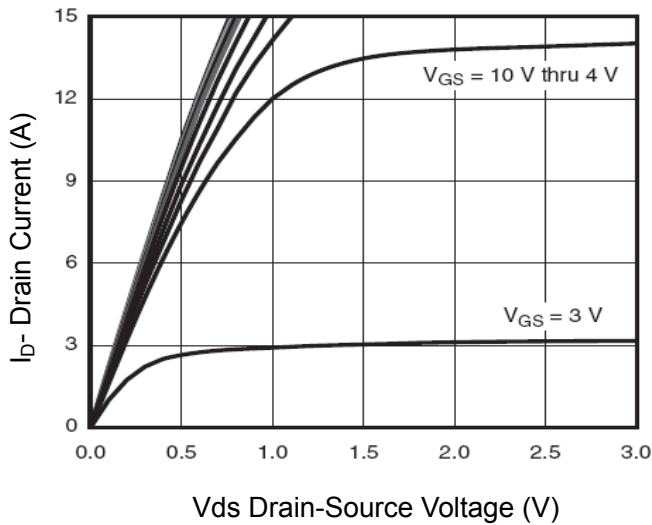
**Figure 2: Switching Waveforms**



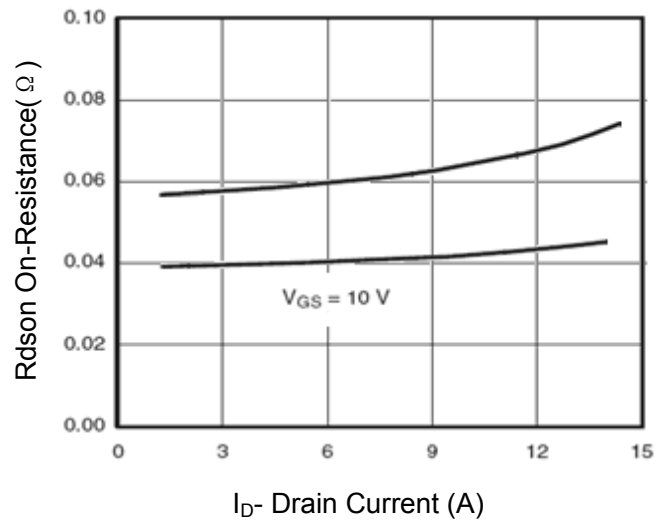
**Figure 3 Power Dissipation**



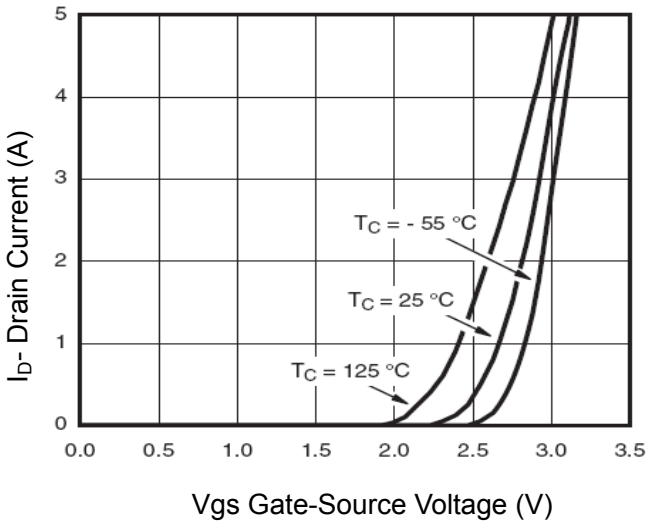
**Figure 4 Drain Current**



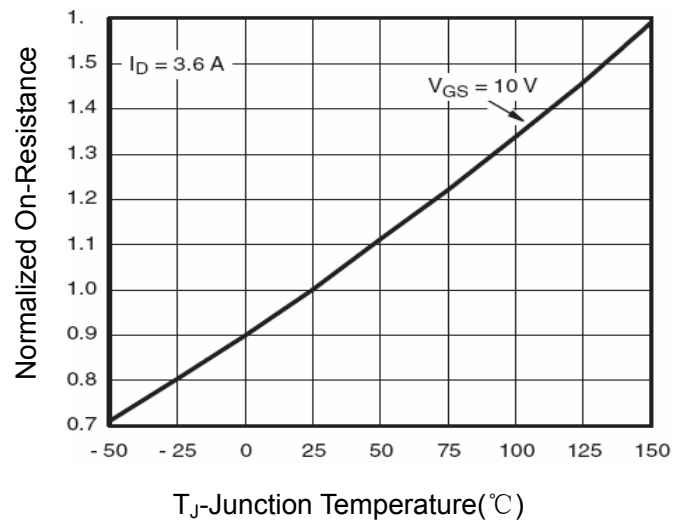
**Figure 5 Output Characteristics**



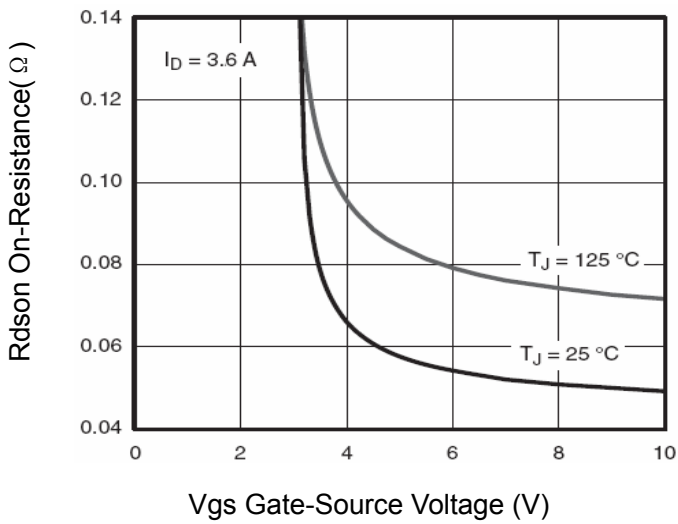
**Figure 6 Drain-Source On-Resistance**



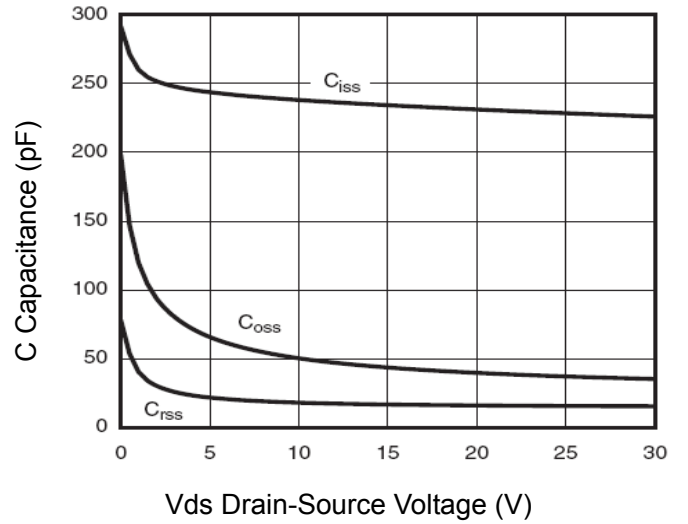
**Figure 7 Transfer Characteristics**



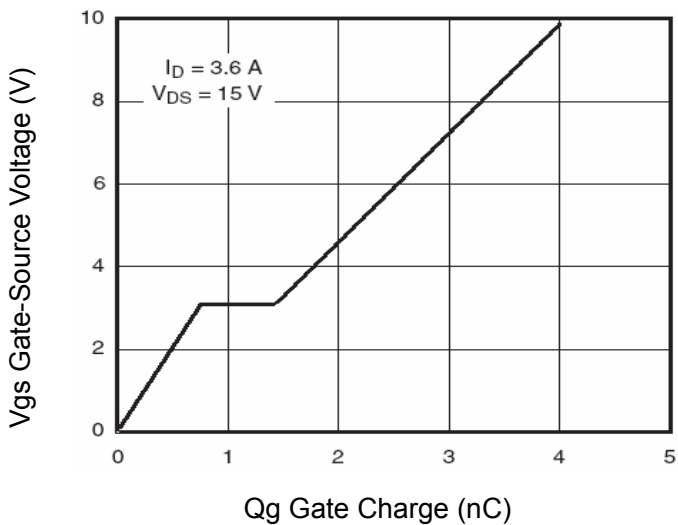
**Figure 8 Drain-Source On-Resistance**



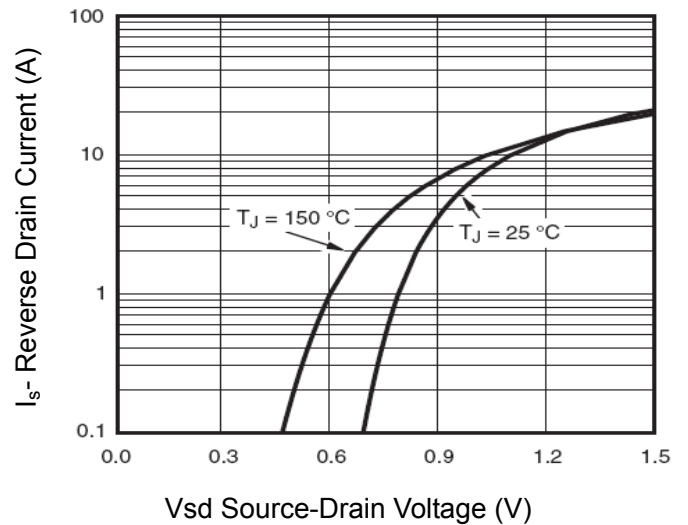
**Figure 9 Rdson vs Vgs**



**Figure 10 Capacitance vs Vds**



**Figure 11 Gate Charge**



**Figure 12 Source- Drain Diode Forward**

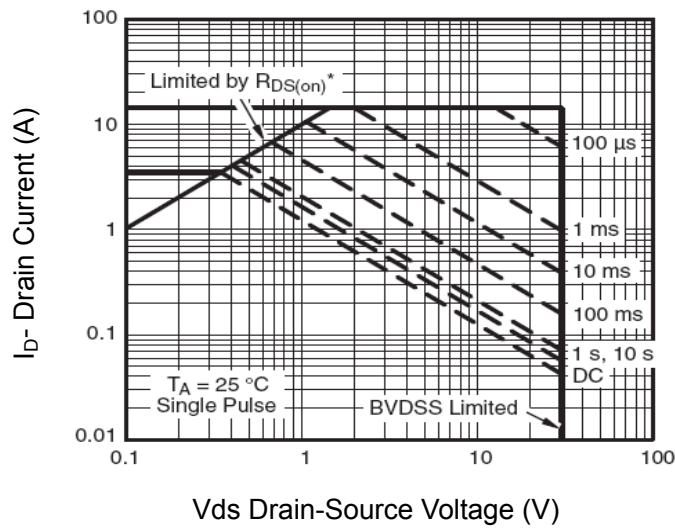


Figure 13 Safe Operation Area

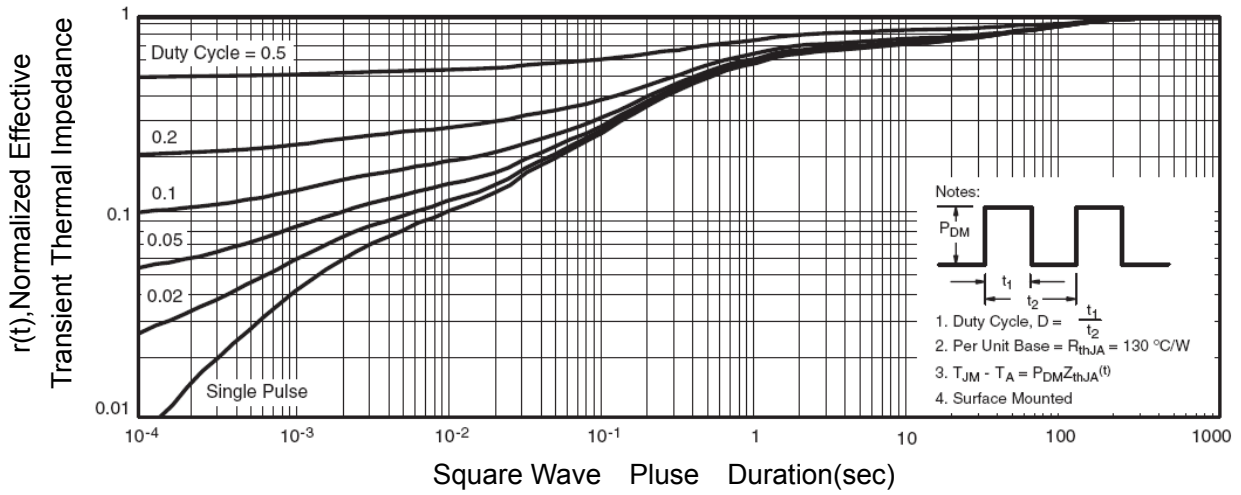
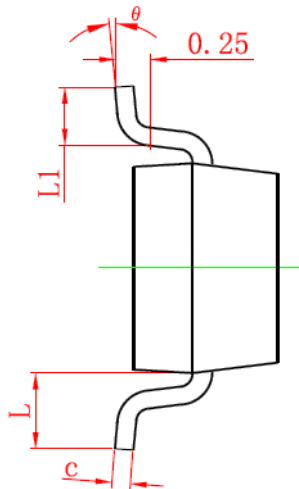
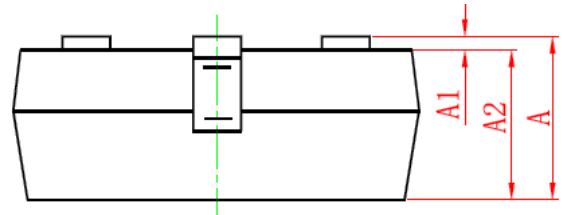
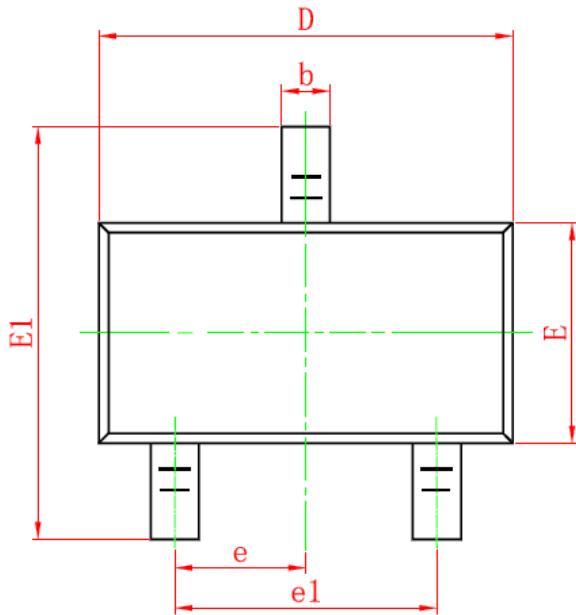


Figure 14 Normalized Maximum Transient Thermal Impedance

**SOT-23 Package Information**


| Symbol                     | Dimensions in Millimeters |              |
|----------------------------|---------------------------|--------------|
|                            | MIN.                      | MAX.         |
| <b>A</b>                   | <b>0.900</b>              | <b>1.150</b> |
| <b>A1</b>                  | <b>0.000</b>              | <b>0.100</b> |
| <b>A2</b>                  | <b>0.900</b>              | <b>1.050</b> |
| <b>b</b>                   | <b>0.300</b>              | <b>0.500</b> |
| <b>c</b>                   | <b>0.080</b>              | <b>0.150</b> |
| <b>D</b>                   | <b>2.800</b>              | <b>3.000</b> |
| <b>E</b>                   | <b>1.200</b>              | <b>1.400</b> |
| <b>E1</b>                  | <b>2.250</b>              | <b>2.550</b> |
| <b>e</b>                   | <b>0.950TYP</b>           |              |
| <b>e1</b>                  | <b>1.800</b>              | <b>2.000</b> |
| <b>L</b>                   | <b>0.550REF</b>           |              |
| <b>L1</b>                  | <b>0.300</b>              | <b>0.500</b> |
| <b><math>\theta</math></b> | <b>0°</b>                 | <b>8°</b>    |

**Notes**

- All dimensions are in millimeters.
- Tolerance  $\pm 0.10\text{mm}$  (4 mil) unless otherwise specified
- Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- Dimension L is measured in gauge plane.
- Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.